SKM100GAL12F4

SEMITRANS® 2

High Speed IGBT4 Modules

SKM100GAL12F4

Target Data

Features

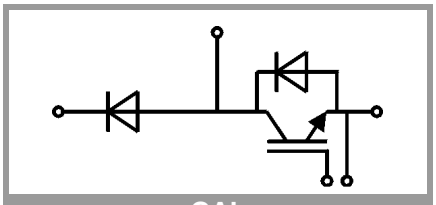
- High speed trench and field-stop IGBT
- CAL4 ultra-fast = soft switching 4. generation CAL-diode
- Insulated copper baseplate using DBC technology (Direct Bonded Copper)
- Increased power cycling capability
- For higher switching frequencies above 15kHz
- UL recognized, file no. E63532

Typical Applications*

- Electronic welders
- DC/DC – converter
- Brake chopper
- Switched reluctance motor

Remarks

- Case temperature limited to T_c = 125°C max.
- Recommended T_{op} = -40 ... +150°C
- Product reliability results valid for T_j = 150°C



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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 175 °C	T_c = 25 °C	142	A
		T_c = 80 °C	109	A
I_{Cnom}			100	A
I_{CRM}	I_{CRM} = 3xI_{Cnom}		300	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 800 V V_{GE} ≤ 15 V V_{CES} ≤ 1200 V	T_j = 150 °C	10	µs
T_j			-40 ... 175	°C
Inverse diode				
V_{RRM}	T_j = 25 °C		1200	V
I_F	T_j = 175 °C	T_c = 25 °C	113	A
		T_c = 80 °C	84	A
I_{Fnom}			100	A
I_{FRM}	I_{FRM} = 2xI_{Fnom}		200	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		490	A
T_j			-40 ... 175	°C
Freewheeling diode				
V_{RRM}	T_j = 25 °C		1200	V
I_F	T_j = 175 °C	T_c = 25 °C	113	A
		T_c = 80 °C	84	A
I_{Fnom}			100	A
I_{FRM}	I_{FRM} = 2xI_{Fnom}		200	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		490	A
T_j			-40 ... 175	°C
Module				
$I_{t(RMS)}$			200	A
T_{stg}	module without TIM		-40 ... 125	°C
V_{isol}	AC sinus 50 Hz, t = 1 min		4000	V

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
$V_{CE(sat)}$	I_C = 100 A V_{GE} = 15 V chiplevel	T_j = 25 °C		2.05	2.38	V
		T_j = 150 °C		2.55	2.93	V
V_{CE0}	chiplevel	T_j = 25 °C		1.10	1.28	V
		T_j = 150 °C		0.95	1.13	V
r_{CE}	V_{GE} = 15 V chiplevel	T_j = 25 °C		9.5	11	mΩ
		T_j = 150 °C		16	18	mΩ
$V_{GE(th)}$	V_{GE}=V_{CE}, I_C = 3.8 mA		5.2	5.8	6.4	V
I_{CES}	V_{GE} = 0 V V_{CE} = 1200 V	T_j = 25 °C			1	mA
		T_j = 150 °C		-		mA
C_{ies}	V_{CE} = 25 V V_{GE} = 0 V	f = 1 MHz		6.2		nF
C_{oes}		f = 1 MHz		0.41		nF
C_{res}		f = 1 MHz		0.35		nF
Q_G	V_{GE} = - 8 V...+ 15 V			567		nC
R_{Gint}	T_j = 25 °C			0		Ω

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- Case temperature limited to T_c = 125°C max.
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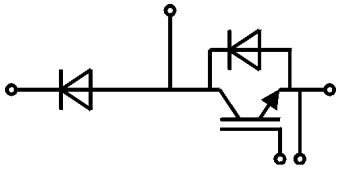
- Product reliability results valid for T_j = 150°C



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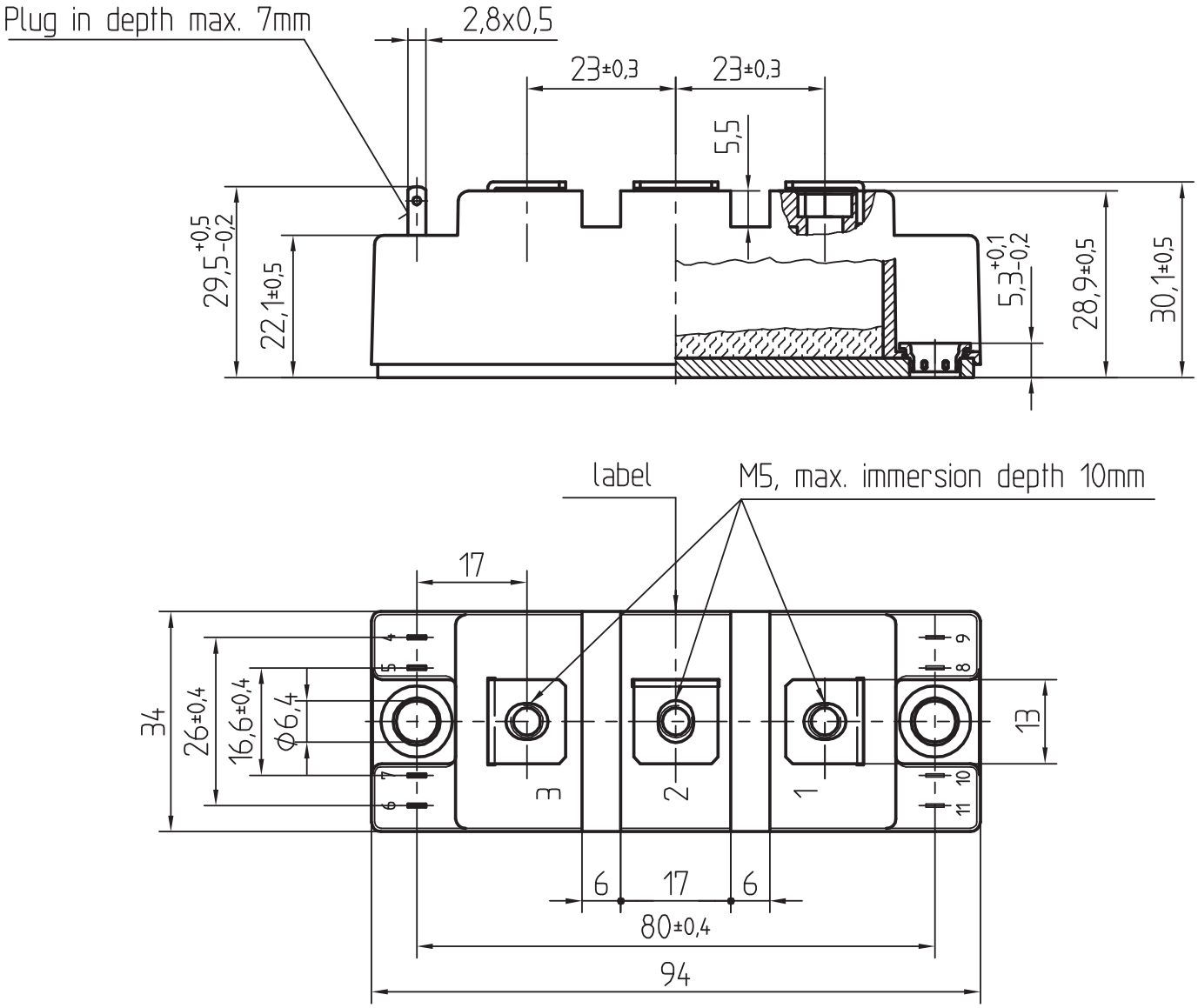
Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
$t_{d(on)}$	V_{CC} = 600 V I_C = 100 A V_{GE} = +15/-15 V $R_{G\ on}$ = 2 Ω $R_{G\ off}$ = 2 Ω	T_j = 150 °C		t.b.d.		ns
t_r		T_j = 150 °C		t.b.d.		ns
E_{on}		T_j = 150 °C		10		mJ
$t_{d(off)}$		T_j = 150 °C		t.b.d.		ns
t_f		T_j = 150 °C		t.b.d.		ns
E_{off}		T_j = 150 °C		7		mJ
$R_{th(j-c)}$	per IGBT				0.27	K/W
$R_{th(c-s)}$	per IGBT (λ_{grease}=0.81 W/(m*K))			0.122		K/W
Inverse diode						
$V_F = V_{EC}$	I_F = 100 A V_{GE} = 0 V chiplevel	T_j = 25 °C		2.53	2.91	V
		T_j = 150 °C		2.49	2.85	V
V_{F0}	chiplevel	T_j = 25 °C		1.53	1.77	V
		T_j = 150 °C		1.12	1.36	V
r_F	chiplevel	T_j = 25 °C		10.0	11	mΩ
		T_j = 150 °C		14	15	mΩ
I_{RRM}	I_F = 100 A V_{GE} = ±15 V V_{CC} = 600 V	T_j = 150 °C		t.b.d.		A
Q_{rr}		T_j = 150 °C		t.b.d.		µC
E_{rr}		T_j = 150 °C		3.8		mJ
$R_{th(j-c)}$	per diode				0.48	K/W
$R_{th(c-s)}$	per diode (λ_{grease}=0.81 W/(m*K))			0.134		K/W
Freewheeling diode						
$V_F = V_{EC}$	I_F = 100 A V_{GE} = 0 V chiplevel	T_j = 25 °C		2.53	2.91	V
		T_j = 150 °C		2.49	2.85	V
V_{F0}	chiplevel	T_j = 25 °C		1.53	1.77	V
		T_j = 150 °C		1.12	1.36	V
r_F	chiplevel	T_j = 25 °C		10.0	11	mΩ
		T_j = 150 °C		14	15	mΩ
I_{RRM}	I_F = 100 A V_{GE} = ±15 V V_{CC} = 600 V	T_j = 150 °C				A
Q_{rr}		T_j = 150 °C				µC
E_{rr}		T_j = 150 °C		3.2		mJ
$R_{th(j-c)}$	per diode				0.48	K/W
$R_{th(c-s)}$	per diode (λ_{grease}=0.81 W/(m*K))			0.134		K/W
Module						
L_{CE}				30		nH
$R_{CC'+EE'}$	measured per switch	T_C = 25 °C		0.65		mΩ
		T_C = 125 °C		1.09		mΩ
$Rth_{(c-s)1}$	calculated without thermal coupling (λ_{grease}=0.81 W/(m*K))			0.064		K/W
$Rth_{(c-s)2}$	including thermal coupling, Ts underneath module (λ_{grease}=0.81 W/(m*K))			0.101		K/W
M_s	to heat sink M6		3		5	Nm
M_t		to terminals M5	2.5		5	Nm
						Nm
w					160	g

Dimensions in mm



General tolerance +/- 0,5 mm

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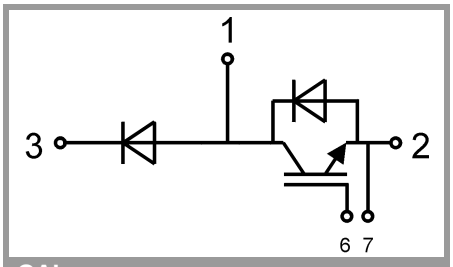

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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